

Guoxing Duan

List of Publications by Year in descending order

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Version: 2024-02-01

6
papers

136
citations

1478505

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1872680

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all docs

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docs citations

6
times ranked

229
citing authors

#	ARTICLE	IF	CITATIONS
1	Bias Dependence of Total Ionizing Dose Effects in SiGe-MOS FinFETs. IEEE Transactions on Nuclear Science, 2014, 61, 2834-2838.	2.0	57
2	Total Ionizing Dose Effects on hBN Encapsulated Graphene Devices. IEEE Transactions on Nuclear Science, 2014, 61, 2868-2873.	2.0	27
3	Electrical Stress and Total Ionizing Dose Effects on MoS_2 Transistors. IEEE Transactions on Nuclear Science, 2014, 61, 2862-2867.	2.0	20
4	Effects of Negative-Bias-Temperature-Instability on Low-Frequency Noise in SiGe p MOSFETs. IEEE Transactions on Device and Materials Reliability, 2016, 16, 541-548.	2.0	16
5	Activation Energies for Oxide- and Interface-Trap Charge Generation Due to Negative-Bias Temperature Stress of Si-Capped SiGe-pMOSFETs. IEEE Transactions on Device and Materials Reliability, 2015, 15, 352-358.	2.0	9
6	Total Ionizing Dose Effects on Ge Channel $\text{Si}_{0.55}\text{Ge}_{0.45}$ FETs with Raised $\text{Si}_{0.55}\text{Ge}_{0.45}$ Source/Drain. IEEE Transactions on Nuclear Science, 2015, 62, 2412-2416.	2.0	7